

CORRECTION

Correction to: Generation and Auto-Revealing of Dislocations in Si During Macropore Etching

K.P. KONIN ^{1,2} O.YO. GUDYMENKO,¹ V.P. KLAD'KO,¹
O.O. LYTVYNENKO,¹ and D.V. MOROZOV'S'KA¹

1.—V. Lashkaryov Institute of Semiconductor Physics, National Academy of Science of Ukraine, Nauki Av. 41, Kiev 03028, Ukraine. 2.—e-mail: kpkonin@isp.kiev.ua

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On page 5116, last paragraph in the XRD Data section, there is an error. The corrected sentence is as follows:

This leads to a temperature gradient greater than 10^3C/cm and a lattice deformation on the order of 10^{-5} .